2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

Future Normal in Semiconductor

2025년 2월 13일(목), 09:00-10:45 Room L(하트II+III), 6층

E. Compound Semiconductors 분과

052_[FL1-E] III-V Semiconductor

좌장: 신승헌 교수(순천향대학교), 심재필 박사(한국나노기술원)

초청 FL1-E-1 09:00-09:30	Accurate Measurement of Wide Bandgap Power Devices' Switching Hyemin Kang Department of Energy Engineering, KENTECH
FL1-E-2 09:30-09:45	L _g = 50 nm In _{0.65} Ga _{0.35} As HEMTs with Record Noise-Figure Performance Min-Seo Yu ¹ , Seung-Woo Son ¹ , Sang-Ki Yun ¹ , Sang-Pyeong Son ¹ , Ji-Hoon Yoo ¹ , Kyounghoon Yang ² , Jae-Hak Lee ¹ , and Dae-Hyun Kim ¹ ¹School of Electronic and Electrical Engineering, Kyungpook National University, ²KAIST
FL1-E-3 09:45-10:00	M3D InGaAs MOSHEMT on Si Substrate with Low Gate Leakage Current Yoon-Je Suh, Jaeyong Jeong, Nahyun Rheem, Chan Jik Lee, and Sanghyeon Kim KAIST
FL1-E-4 10:00-10:15	$\label{eq:Lg} \begin{array}{l} \textbf{L}_{g} = \textbf{50 nm Gate-All-Around In}_{0.53}\textbf{Ga}_{0.47}\textbf{As Nanosheet MOSFETs} \\ \textbf{JH. Yoo}^{1}, \textbf{HB. Jo}^{1}, {}^{2}, \textbf{IG. Lee}^{1}, \textbf{SM. Choi}^{1}, \textbf{HJ. Kim}^{1}, \textbf{WS. Park}^{1}, \textbf{H. Jang}^{3}, \textbf{CS. Shin}^{3}, \textbf{KS. Seo}^{3}, \textbf{SK. Kim}^{4}, \textbf{JG. Kim}^{4}, \textbf{J. Yun}^{4}, \textbf{T. Kim}^{4}, \textbf{JH. Lee}^{1}, \textbf{and DH. Kim}^{1} \\ {}^{1}\textbf{Kyungpook National University, } {}^{2}\textbf{KETI, } {}^{3}\textbf{KANC, } {}^{4}\textbf{QSI} \end{array}$
FL1-E-5 10:15-10:30	Study of 1.65 eV Al0.18Ga0.82As Tunnel Junction with Hybrid Delta-Doped n-GaAs Quantum Well for Monolithic III-V/Si Tandem Solar Cells Eunkyo Ju ^{1,2} , May Angelu Madarang ^{1,3} , Yeonhwa Kim ^{1,2} , Rafael Jumar Chu ^{1,3} , Tsimafei Laryn ^{1,3} , In-Hwan Lee ² , Won Jun Choi ¹ , and Daehwan Jung ^{1,3} ¹Center for Quantum Technology, KIST, ²Department of Materials Science and Engineering, Korea University, ³Division of Nanoscience and Technology, University of Science and Technology



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	Integration of InGaAs/InP Heterojunction Phototransistor on Si CMOS
FL1-E-6	Platform by Wafer Bonding
10:30-10:45	Kyunghwan Kim, Dae-Hwan Ahn, and Jae-Hoon Han
	Center for Quantum Technology, KIST